

Symbol	Typ	Titel
G	Sektion	SECTION G — PHYSICS
G11	Klasse	INFORMATION STORAGE
G11C	Unterklasse	STATIC STORES (information storage based on relative movement between record carrier and transducer G11B; semiconductor devices for storage H01L, e.g. H01L 27/108-H01L 27/115; pulse technique in general H03K, e.g. electronic switches H03K 17/00)
G11C 5/00	Hauptgruppe	Details of stores covered by group G11C 11/00
G11C 5/02	1-Punkt Untergruppe	. Disposition of storage elements, e.g. in the form of a matrix array
G11C 5/04	2-Punkt Untergruppe	. . Supports for storage elements; Mounting or fixing of storage elements on such supports
G11C 5/05	3-Punkt Untergruppe	. . . Supporting of cores in matrix [2]
G11C 5/06	1-Punkt Untergruppe	. Arrangements for interconnecting storage elements electrically, e.g. by wiring
G11C 5/08	2-Punkt Untergruppe	. . for interconnecting magnetic elements, e.g. toroidal cores
G11C 5/10	2-Punkt Untergruppe	. . for interconnecting capacitors
G11C 5/12	1-Punkt Untergruppe	. Apparatus or processes for interconnecting storage elements, e.g. for threading magnetic cores
G11C 5/14	1-Punkt Untergruppe	. Power supply arrangements (auxiliary circuits for stores using semiconductor devices G11C 11/4063, G11C 11/413, G11C 11/4193; in general G05F, H02J, H02M) [5, 7]
G11C 7/00	Hauptgruppe	Arrangements for writing information into, or reading information out from, a digital store (G11C 5/00 takes precedence; auxiliary circuits for stores using semiconductor devices G11C 11/4063, G11C 11/413, G11C 11/4193) [2, 5]
G11C 7/02	1-Punkt Untergruppe	. with means for avoiding parasitic signals
G11C 7/04	1-Punkt Untergruppe	. with means for avoiding disturbances due to temperature effects
G11C 7/06	1-Punkt Untergruppe	. Sense amplifiers; Associated circuits (amplifiers <u>per se</u> H03F, H03K) [1, 7]
G11C 7/08	2-Punkt Untergruppe	. . Control thereof [7]
G11C 7/10	1-Punkt Untergruppe	. Input/output (I/O) data interface arrangements, e.g. I/O data control circuits, I/O data buffers (level conversion circuits in general H03K 19/0175) [7]
G11C 7/12	1-Punkt Untergruppe	. Bit line control circuits, e.g. drivers, boosters, pull-up circuits, pull-down circuits, precharging circuits, equalising circuits, for bit lines [7]
G11C 7/14	1-Punkt Untergruppe	. Dummy cell management; Sense reference voltage generators [7]
G11C 7/16	1-Punkt Untergruppe	. Storage of analogue signals in digital stores using an arrangement comprising analogue/digital (A/D) converters, digital memories and digital/analogue (D/A) converters [7]
G11C 7/18	1-Punkt Untergruppe	. Bit line organisation; Bit line lay-out [7]
G11C 7/20	1-Punkt Untergruppe	. Memory cell initialisation circuits, e.g. when powering up or down, memory clear, latent image memory [7]
G11C 7/22	1-Punkt Untergruppe	. Read-write (R-W) timing or clocking circuits; Read-write (R-W) control signal generators or management [7]
G11C 7/24	1-Punkt Untergruppe	. Memory cell safety or protection circuits, e.g. arrangements for preventing inadvertent reading or writing; Status cells; Test cells [7]
G11C 8/00	Hauptgruppe	Arrangements for selecting an address in a digital store (auxiliary circuits for stores using semiconductor devices G11C 11/4063, G11C 11/413, G11C 11/4193) [2, 5]
G11C 8/02	1-Punkt Untergruppe	. using selecting matrix [2]

Symbol	Typ	Titel
G11C 8/04	1-Punkt Untergruppe	. using a sequential addressing device, e.g. shift register, counter (using first in first out (FIFO) registers for changing speed of digital data flow G06F 5/06; using last in first out (LIFO) registers for processing digital data by operating upon their order G06F 7/00) [5]
G11C 8/06	1-Punkt Untergruppe	. Address interface arrangements, e.g. address buffers (level conversion circuits in general H03K 19/0175) [7]
G11C 8/08	1-Punkt Untergruppe	. Word line control circuits, e.g. drivers, boosters, pull-up circuits, pull-down circuits, precharging circuits, for word lines [7]
G11C 8/10	1-Punkt Untergruppe	. Decoders [7]
G11C 8/12	1-Punkt Untergruppe	. Group selection circuits, e.g. for memory block selection, chip selection, array selection [7]
G11C 8/14	1-Punkt Untergruppe	. Word line organisation; Word line lay-out [7]
G11C 8/16	1-Punkt Untergruppe	. Multiple access memory array, e.g. addressing one storage element via at least two independent addressing line groups [7]
G11C 8/18	1-Punkt Untergruppe	. Address timing or clocking circuits; Address control signal generation or management, e.g. for row address strobe (RAS) or column address strobe (CAS) signals [7]
G11C 8/20	1-Punkt Untergruppe	. Address safety or protection circuits, i.e. arrangements for preventing unauthorized or accidental access [7]
G11C 11/00	Hauptgruppe	Digital stores characterised by the use of particular electric or magnetic storage elements; Storage elements therefor (G11C 14/00-G11C 21/00 take precedence) [5]
G11C 11/02	1-Punkt Untergruppe	. using magnetic elements
G11C 11/04	2-Punkt Untergruppe	. . using storage elements having cylindrical form, e.g. rod, wire (G11C 11/12, G11C 11/14 take precedence) [2]
G11C 11/06	2-Punkt Untergruppe	. . using single-aperture storage elements, e.g. ring core; using multi-aperture plates in which each individual aperture forms a storage element
G11C 11/061	3-Punkt Untergruppe	. . . using elements with single aperture or magnetic loop for storage, one element per bit, and for destructive read-out [2]
G11C 11/063	4-Punkt Untergruppe bit-organized, such as, 2L/2D-, 3D-organization, i.e. for selection of an element by means of at least two coincident partial currents both for reading and for writing [2]
G11C 11/065	4-Punkt Untergruppe word-organized, such as 2D-organization, or linear selection, i.e. for selection of all the elements of a word by means of a single full current for reading [2]
G11C 11/067	3-Punkt Untergruppe	. . . using elements with single aperture or magnetic loop for storage, one element per bit, and for non-destructive read-out [2]
G11C 11/08	2-Punkt Untergruppe	. . using multi-aperture storage elements, e.g. using transfluxors; using plates incorporating several individual multi-aperture storage elements (G11C 11/10 takes precedence; using multi-aperture plates in which each individual aperture forms a storage element G11C 11/06) [2]
G11C 11/10	2-Punkt Untergruppe	. . using multi-axial storage elements
G11C 11/12	2-Punkt Untergruppe	. . using tensors; using twistors, i.e. elements in which one axis of magnetisation is twisted
G11C 11/14	2-Punkt Untergruppe	. . using thin-film elements
G11C 11/15	3-Punkt Untergruppe	. . . using multiple magnetic layers (G11C 11/155 takes precedence) [2]
G11C 11/155	3-Punkt Untergruppe	. . . with cylindrical configuration [2]
G11C 11/16	2-Punkt Untergruppe	. . using elements in which the storage effect is based on magnetic spin effect
G11C 11/18	1-Punkt Untergruppe	. using Hall-effect devices

Symbol	Typ	Titel
G11C 11/19	1-Punkt Untergruppe	. using non-linear reactive devices in resonant circuits [2]
G11C 11/20	2-Punkt Untergruppe	. . using parametrons [2]
G11C 11/21	1-Punkt Untergruppe	. using electric elements [2]
G11C 11/22	2-Punkt Untergruppe	. . using ferroelectric elements [2]
G11C 11/23	2-Punkt Untergruppe	. . using electrostatic storage on a common layer, e.g. Forrester-Haeff tubes (G11C 11/22 takes precedence) [2]
G11C 11/24	2-Punkt Untergruppe	. . using capacitors (G11C 11/22 takes precedence; using a combination of semiconductor devices and capacitors G11C 11/34, e.g. G11C 11/40) [2, 5]
G11C 11/26	2-Punkt Untergruppe	. . using discharge tubes [2]
G11C 11/28	3-Punkt Untergruppe	. . . using gas-filled tubes [2]
G11C 11/30	3-Punkt Untergruppe	. . . using vacuum tubes (G11C 11/23 takes precedence) [2]
G11C 11/34	2-Punkt Untergruppe	. . using semiconductor devices [2]
G11C 11/35	3-Punkt Untergruppe	. . . with charge storage in a depletion layer, e.g. charge coupled devices [7]
G11C 11/36	3-Punkt Untergruppe	. . . using diodes, e.g. as threshold elements [2]
G11C 11/38	4-Punkt Untergruppe using tunnel diodes [2]
G11C 11/39	3-Punkt Untergruppe	. . . using thyristors [5]
G11C 11/40	3-Punkt Untergruppe	. . . using transistors [2]
G11C 11/401	4-Punkt Untergruppe forming cells needing refreshing or charge regeneration, i.e. dynamic cells [5]
G11C 11/402	5-Punkt Untergruppe with charge regeneration individual to each memory cell, i.e. internal refresh [5]
G11C 11/403	5-Punkt Untergruppe with charge regeneration common to a multiplicity of memory cells, i.e. external refresh [5]
G11C 11/404	6-Punkt Untergruppe with one charge-transfer gate, e.g. MOS transistor, per cell [5]
G11C 11/405	6-Punkt Untergruppe with three charge-transfer gates, e.g. MOS transistors, per cell [5]
G11C 11/406	5-Punkt Untergruppe Management or control of the refreshing or charge-regeneration cycles [5]
G11C 11/4063	5-Punkt Untergruppe Auxiliary circuits, e.g. for addressing, decoding, driving, writing, sensing or timing [7]
G11C 11/4067	6-Punkt Untergruppe for memory cells of the bipolar type [7]
G11C 11/407	6-Punkt Untergruppe for memory cells of the field-effect type [5]
G11C 11/4072	7-Punkt Untergruppe Circuits for initialization, powering up or down, clearing memory or presetting [7]
G11C 11/4074	7-Punkt Untergruppe Power supply or voltage generation circuits, e.g. bias voltage generators, substrate voltage generators, back-up power, power control circuits [7]
G11C 11/4076	7-Punkt Untergruppe Timing circuits (for regeneration management G11C 11/406) [7]
G11C 11/4078	7-Punkt Untergruppe Safety or protection circuits, e.g. for preventing inadvertent or unauthorised reading or writing; Status cells; Test cells (protection of memory contents during checking or testing G11C 29/52) [7]
G11C 11/408	7-Punkt Untergruppe Address circuits [5]
G11C 11/409	7-Punkt Untergruppe Read-write (R-W) circuits [5]

Symbol	Typ	Titel
G11C 11/4091	8-Punkt Untergruppe Sense or sense/refresh amplifiers, or associated sense circuitry, e.g. for coupled bit-line precharging, equalising or isolating [7]
G11C 11/4093	8-Punkt Untergruppe Input/output (I/O) data interface arrangements, e.g. data buffers (level conversion circuits in general H03K 19/0175) [7]
G11C 11/4094	8-Punkt Untergruppe Bit-line management or control circuits [7]
G11C 11/4096	8-Punkt Untergruppe Input/output (I/O) data management or control circuits, e.g. reading or writing circuits, I/O drivers, bit-line switches [7]
G11C 11/4097	8-Punkt Untergruppe Bit-line organisation, e.g. bit-line layout, folded bit lines [7]
G11C 11/4099	8-Punkt Untergruppe Dummy cell treatment; Reference voltage generators [7]
G11C 11/41	4-Punkt Untergruppe forming cells with positive feedback, i.e. cells not needing refreshing or charge regeneration, e.g. bistable multivibrator or Schmitt trigger [5]
G11C 11/411	5-Punkt Untergruppe using bipolar transistors only [5]
G11C 11/412	5-Punkt Untergruppe using field-effect transistors only [5]
G11C 11/413	5-Punkt Untergruppe Auxiliary circuits, e.g. for addressing, decoding, driving, writing, sensing, timing or power reduction [5]
G11C 11/414	6-Punkt Untergruppe for memory cells of the bipolar type [5]
G11C 11/415	7-Punkt Untergruppe Address circuits [5]
G11C 11/416	7-Punkt Untergruppe Read-write (R-W) circuits [5]
G11C 11/417	6-Punkt Untergruppe for memory cells of the field-effect type [5]
G11C 11/418	7-Punkt Untergruppe Address circuits [5]
G11C 11/419	7-Punkt Untergruppe Read-write (R-W) circuits [5]
G11C 11/4193	3-Punkt Untergruppe	. . . Auxiliary circuits specific to particular types of semiconductor storage devices, e.g. for addressing, driving, sensing, timing, power supply, signal propagation (G11C 11/4063, G11C 11/413 take precedence) [7]
G11C 11/4195	4-Punkt Untergruppe Address circuits [7]
G11C 11/4197	4-Punkt Untergruppe Read-write (R-W) circuits [7]
G11C 11/42	2-Punkt Untergruppe	. . using opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled
G11C 11/44	2-Punkt Untergruppe	. . using super-conductive elements, e.g. cryotron [2]
G11C 11/46	1-Punkt Untergruppe	. using thermoplastic elements
G11C 11/48	1-Punkt Untergruppe	. using displaceable coupling elements, e.g. ferromagnetic cores, to produce change between different states of mutual or self-inductance
G11C 11/50	1-Punkt Untergruppe	. using actuation of electric contacts to store the information (mechanical stores G11C 23/00; switches providing a selected number of consecutive operations of the contacts by a single manual actuation of the operating part H01H 41/00)
G11C 11/52	2-Punkt Untergruppe	. . using electromagnetic relays
G11C 11/54	1-Punkt Untergruppe	. using elements simulating biological cells, e.g. neuron
G11C 11/56	1-Punkt Untergruppe	. using storage elements with more than two stable states represented by steps, e.g. of voltage, current, phase, frequency (counting arrangements comprising multi-stable elements of this type H03K 25/00, H03K 29/00) [2]

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G11C 13/00	Hauptgruppe	Digital stores characterised by the use of storage elements not covered by groups G11C 11/00, G11C 23/00, or G11C 25/00
G11C 13/02	1-Punkt Untergruppe	. using elements whose operation depends upon chemical change (using electrochemical charge G11C 11/00)
G11C 13/04	1-Punkt Untergruppe	. using optical elements
G11C 13/06	2-Punkt Untergruppe	. . using magneto-optical elements (magneto-optics in general G02F) [2]
G11C 14/00	Hauptgruppe	Digital stores characterised by arrangements of cells having volatile and non-volatile storage properties for back-up when the power is down [5]
G11C 15/00	Hauptgruppe	Digital stores in which information comprising one or more characteristic parts is written into the store and in which information is read-out by searching for one or more of these characteristic parts, i.e. associative or content-addressed stores (in which information is addressed to a specific location G11C 11/00) [2]
G11C 15/02	1-Punkt Untergruppe	. using magnetic elements [2]
G11C 15/04	1-Punkt Untergruppe	. using semiconductor elements [2]
G11C 15/06	1-Punkt Untergruppe	. using cryogenic elements [2]
G11C 16/00	Hauptgruppe	Erasable programmable read-only memories (G11C 14/00 takes precedence) [5]
G11C 16/02	1-Punkt Untergruppe	. electrically programmable [5]
G11C 16/04	2-Punkt Untergruppe	. . using variable threshold transistors, e.g. FAMOS [5]
G11C 16/06	2-Punkt Untergruppe	. . Auxiliary circuits, e.g. for writing into memory (in general G11C 7/00) [5]
G11C 16/08	3-Punkt Untergruppe	. . . Address circuits; Decoders; Word-line control circuits [7]
G11C 16/10	3-Punkt Untergruppe	. . . Programming or data input circuits [7]
G11C 16/12	4-Punkt Untergruppe Programming voltage switching circuits [7]
G11C 16/14	4-Punkt Untergruppe Circuits for erasing electrically, e.g. erase voltage switching circuits [7]
G11C 16/16	5-Punkt Untergruppe for erasing blocks, e.g. arrays, words, groups [7]
G11C 16/18	4-Punkt Untergruppe Circuits for erasing optically [7]
G11C 16/20	4-Punkt Untergruppe Initialising; Data preset; Chip identification [7]
G11C 16/22	3-Punkt Untergruppe	. . . Safety or protection circuits preventing unauthorised or accidental access to memory cells [7]
G11C 16/24	3-Punkt Untergruppe	. . . Bit-line control circuits [7]
G11C 16/26	3-Punkt Untergruppe	. . . Sensing or reading circuits; Data output circuits [7]
G11C 16/28	4-Punkt Untergruppe using differential sensing or reference cells, e.g. dummy cells [7]
G11C 16/30	3-Punkt Untergruppe	. . . Power supply circuits [7]
G11C 16/32	3-Punkt Untergruppe	. . . Timing circuits [7]
G11C 16/34	3-Punkt Untergruppe	. . . Determination of programming status, e.g. threshold voltage, overprogramming or underprogramming, retention [7]
G11C 17/00	Hauptgruppe	Read-only memories programmable only once; Semi-permanent stores, e.g. manually-replaceable information cards (erasable programmable read-only memories G11C 16/00; coding, decoding or code conversion, in general H03M) [2, 5]
G11C 17/02	1-Punkt Untergruppe	. using magnetic or inductive elements (G11C 17/14 takes precedence) [2, 5]
G11C 17/04	1-Punkt Untergruppe	. using capacitive elements (G11C 17/06, G11C 17/14 take precedence) [2, 5]

Symbol	Typ	Titel
G11C 17/06	1-Punkt Untergruppe	. using diode elements (G11C 17/14 takes precedence) [2, 5]
G11C 17/08	1-Punkt Untergruppe	. using semiconductor devices, e.g. bipolar elements (G11C 17/06, G11C 17/14 take precedence) [5]
G11C 17/10	2-Punkt Untergruppe	. . in which contents are determined during manufacturing by a predetermined arrangement of coupling elements, e.g. mask-programmable ROM [5]
G11C 17/12	3-Punkt Untergruppe	. . . using field-effect devices [5]
G11C 17/14	1-Punkt Untergruppe	. in which contents are determined by selectively establishing, breaking or modifying connecting links by permanently altering the state of coupling elements, e.g. PROM [5]
G11C 17/16	2-Punkt Untergruppe	. . using electrically-fusible links [5]
G11C 17/18	2-Punkt Untergruppe	. . Auxiliary circuits, e.g. for writing into memory (in general G11C 7/00) [5]
G11C 19/00	Hauptgruppe	Digital stores in which the information is moved stepwise, e.g. shift registers (counting chains H03K 23/00)
G11C 19/02	1-Punkt Untergruppe	. using magnetic elements (G11C 19/14 takes precedence) [2]
G11C 19/04	2-Punkt Untergruppe	. . using cores with one aperture or magnetic loop [2]
G11C 19/06	2-Punkt Untergruppe	. . using structures with a number of apertures or magnetic loops, e.g. transfluxors [2]
G11C 19/08	2-Punkt Untergruppe	. . using thin films in plane structure [2]
G11C 19/10	2-Punkt Untergruppe	. . using thin films on rods; with twistors [2]
G11C 19/12	1-Punkt Untergruppe	. using non-linear reactive devices in resonant circuits [2]
G11C 19/14	1-Punkt Untergruppe	. using magnetic elements in combination with active elements, e.g. discharge tubes, semiconductor elements (G11C 19/34 takes precedence) [2, 7]
G11C 19/18	1-Punkt Untergruppe	. using capacitors as main elements of the stages [2]
G11C 19/20	1-Punkt Untergruppe	. using discharge tubes (G11C 19/14 takes precedence) [2]
G11C 19/28	1-Punkt Untergruppe	. using semiconductor elements (G11C 19/14, G11C 19/36 take precedence) [2, 7]
G11C 19/30	1-Punkt Untergruppe	. using opto-electronic devices, i.e. light-emitting and photoelectric devices electrically- or optically-coupled [2]
G11C 19/32	1-Punkt Untergruppe	. using super-conductive elements [2]
G11C 19/34	1-Punkt Untergruppe	. using storage elements with more than two stable states represented by steps, e.g. of voltage, current, phase, frequency [7]
G11C 19/36	2-Punkt Untergruppe	. . using semiconductor elements [7]
G11C 19/38	1-Punkt Untergruppe	. two-dimensional, e.g. horizontal and vertical shift registers [7]
G11C 21/00	Hauptgruppe	Digital stores in which the information circulates (stepwise G11C 19/00)
G11C 21/02	1-Punkt Untergruppe	. using electromechanical delay lines, e.g. using a mercury tank
G11C 23/00	Hauptgruppe	Digital stores characterised by movement of mechanical parts to effect storage, e.g. using balls; Storage elements therefor (storing by actuating contacts G11C 11/48)
G11C 25/00	Hauptgruppe	Digital stores characterised by the use of flowing media; Storage elements therefor
G11C 27/00	Hauptgruppe	Electric analogue stores, e.g. for storing instantaneous values
G11C 27/02	1-Punkt Untergruppe	. Sample-and-hold arrangements (G11C 27/04 takes precedence; sampling electrical signals, in general H03K) [2, 4]

Symbol	Typ	Titel
G11C 27/04	1-Punkt Untergruppe	. Shift registers (charge coupled devices <u>per se</u> H01L 29/76) [4]
G11C 29/00	Hauptgruppe	Checking stores for correct operation ; Testing stores during standby or offline operation [1, 2006.01]
G11C 29/02	1-Punkt Untergruppe	. Detection or location of defective auxiliary circuits, e.g. defective refresh counters [2006.01]
G11C 29/04	1-Punkt Untergruppe	. Detection or location of defective memory elements [2006.01]
G11C 29/06	2-Punkt Untergruppe	.. Acceleration testing [2006.01]
G11C 29/08	2-Punkt Untergruppe	.. Functional testing, e.g. testing during refresh, power-on self testing (POST) or distributed testing [2006.01]
G11C 29/10	3-Punkt Untergruppe	... Test algorithms, e.g. memory scan (MScan) algorithms ; Test patterns, e.g. checkerboard patterns [2006.01]
G11C 29/12	3-Punkt Untergruppe	... Built-in arrangements for testing, e.g. built-in self testing (BIST) [2006.01]
G11C 29/14	4-Punkt Untergruppe Implementation of control logic, e.g. test mode decoders [2006.01]
G11C 29/16	5-Punkt Untergruppe using microprogrammed units, e.g. state machines [2006.01]
G11C 29/18	4-Punkt Untergruppe Address generation devices ; Devices for accessing memories, e.g. details of addressing circuits [2006.01]
G11C 29/20	5-Punkt Untergruppe using counters or linear-feedback shift registers (LFSR) [2006.01]
G11C 29/22	5-Punkt Untergruppe Accessing serial memories [2006.01]
G11C 29/24	5-Punkt Untergruppe Accessing extra cells, e.g. dummy cells or redundant cells [2006.01]
G11C 29/26	5-Punkt Untergruppe Accessing multiple arrays (G11C 29/24 takes precedence) [2006.01]
G11C 29/28	6-Punkt Untergruppe Dependent multiple arrays, e.g. multi-bit arrays [2006.01]
G11C 29/30	5-Punkt Untergruppe Accessing single arrays [2006.01]
G11C 29/32	6-Punkt Untergruppe Serial access ; Scan testing [2006.01]
G11C 29/34	6-Punkt Untergruppe Accessing multiple bits simultaneously [2006.01]
G11C 29/36	4-Punkt Untergruppe Data generation devices, e.g. data inverters [2006.01]
G11C 29/38	4-Punkt Untergruppe Response verification devices [2006.01]
G11C 29/40	5-Punkt Untergruppe using compression techniques [2006.01]
G11C 29/42	5-Punkt Untergruppe using error correcting codes (ECC) or parity check [2006.01]
G11C 29/44	4-Punkt Untergruppe Indication or identification of errors, e.g. for repair [2006.01]
G11C 29/46	4-Punkt Untergruppe Test trigger logic [2006.01]
G11C 29/48	3-Punkt Untergruppe	... Arrangements in static stores specially adapted for testing by means external to the store, e.g. using direct memory access (DMA) or using auxiliary access paths (external testing equipment G11C 29/56) [2006.01]
G11C 29/50	2-Punkt Untergruppe	.. Marginal testing, e.g. race, voltage or current testing [2006.01]
G11C 29/52	1-Punkt Untergruppe	. Protection of memory contents ; Detection of errors in memory contents [2006.01]
G11C 29/54	1-Punkt Untergruppe	. Arrangements for designing test circuits, e.g. design for test (DFT) tools [2006.01]

Symbol	Typ	Titel
<i>G11C 29/56</i>	<i>1-Punkt Untergruppe</i>	<i>External testing equipment for static stores, e.g. automatic test equipment (ATE); Interfaces therefor [2006.01]</i>
G11C 99/00	Hauptgruppe	Subject matter not provided for in other groups of this subclass [2006.01]